

NPN Phototransistor

OP804SL, OP805SL, OP830SL

OP800WSL, OP801WSL, OP802WSL, OP830WSL

Obsolete (OP800SL)

Features:

- TO-18 hermetically sealed package
- Mechanically and spectrally matched to OP130 and OP230 LEDs
- TX and TXV process available (see Hi-Rel section)
- Choice of narrow or wide receiving angle
- Variety of sensitivity ranges
- Enhanced temperature range



"WSL"

Description:

Each device in this series consists of a NPN silicon phototransistor mounted in a hermetically sealed TO-18 package that offers high power dissipation and superior hostile environment operation. The **OP800SL (Obsolete)**, **OP804SL**, **OP805SL** and **OP830SL** devices have a narrow receiving angle that provides excellent on-axis coupling and a bonded base lead that enables conventional transistor biasing. The **OP800WSL**, **OP801WSL**, **OP802WSL** and **OP830WSL** all have a wide receiving angle that provides relatively even reception over a large area.

Devices are 100% production tested using an infrared light source for close correlation with OPTEK's GaAs and GaAlAs emitters. *The OP800SL and devices are mechanically and spectrally matched to OP130 and OP230 series LEDs. The OP800WSL devices are mechanically and spectrally matched to OP130W and OP230W series devices.*

Please refer to Application Bulletins 208 and 210 for additional design information and reliability (degradation) data.

Applications:

- Space-limited applications
- Hostile environment applications
- Applications requiring high power dissipation

Part Number Guide — OPXXX

OPTEK Component
8 — TO-18 Package
0 — Phototransistor
3 — Photodarlington

OP XXXX

SL — Tested at 2870° K
WSL — Tested at 2870° K

Part Description:

OP80__SL = TO-18 dome lens, phototransistor
4 and 5 sensitivity levels
tested with 2870° K light source

OP80__WSL = TO-18 flat lens, phototransistor
0 through 2 sensitivity levels
tested with 2870° K light source

OP830SL = TO-18 dome lens, photodarlington
tested with 2870° K light source

OP830WSL = TO-18 flat lens, photodarlington
tested with 2870° K light source



RoHS

General Note

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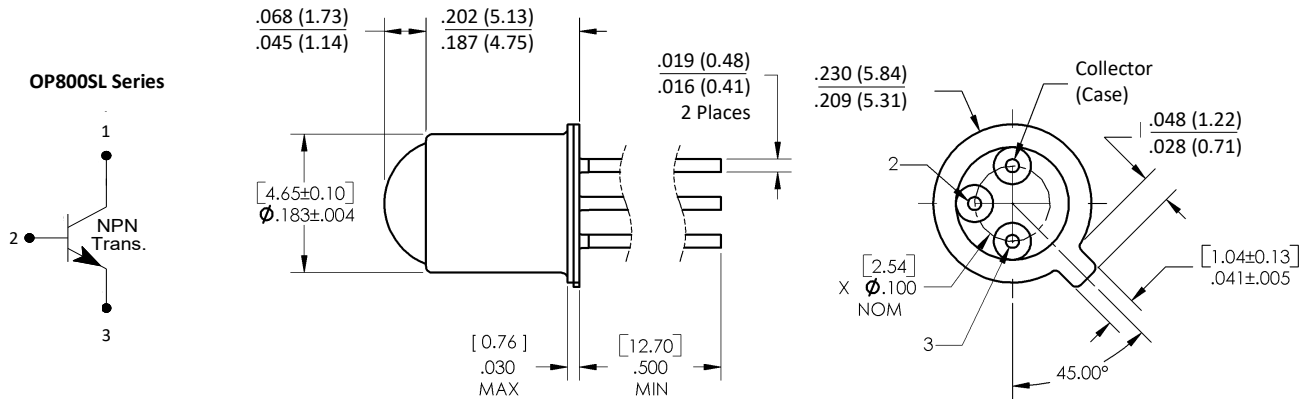
OP804SL, OP805SL, OP830SL

OP800WSL, OP801WSL, OP802WSL, OP830WSL

Obsolete (OP800SL)

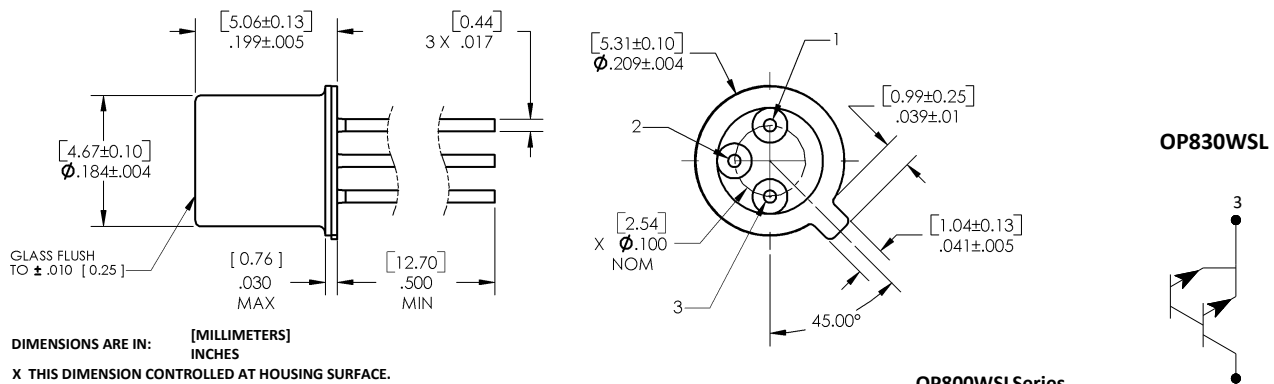


OP800SL, OP830SL

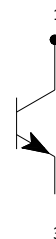


Pin #	OP80X	OP830
1	Collector	Collector
2	Base	—
3	Emitter	Emitter

OP800WSL, OP830WSL



OP800WSL Series



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Obsolete (OP800SL)



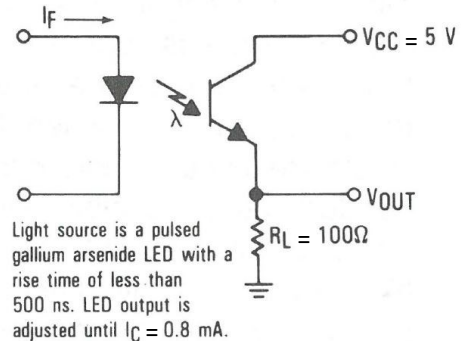
Electrical Specifications

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)	
Storage Temperature Range	-65°C to $+150^\circ\text{C}$
Operating Temperature Range	-65°C to $+125^\circ\text{C}$
Collector-Base Voltage (applies to OP800SL only - does not apply to OP800WSL)	30 V
Collector-Emitter Voltage OP800 (SL, WSL) OP830 (SL, WSL)	30 V 15 V
Emitter-Base Voltage (applies to OP800 (SL, WSL) only)	5 V
Emitter-Collector Voltage (applies to all OP800 and OP830 devices)	5 V
Continuous Collector Current	50 mA
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 seconds with soldering iron]	$260^\circ\text{C}^{(1)}$
Power Dissipation	$250\text{ mW}^{(2)}$

Notes:

1. RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering. A maximum 20 grams force may be applied to the leads when soldering.
2. Derate linearly $2.5\text{ mW}/^\circ\text{C}$ above 25°C .
3. Junction temperature maintained at 25°C .
4. Light source is an unfiltered tungsten bulb operating at $CT = 2870\text{ K}$.

Switching Time Test Circuit



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Obsolete (OP800SL)



Electrical Specifications

Electrical Characteristics (T _A = 25° C unless otherwise noted)						
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
I _{C(ON)} ⁽³⁾	On-State Collector Current					
	OP800SL	0.5	-	-		V _{CE} = 5 V, E _E = 2.5 mW/cm ²⁽²⁾⁽³⁾⁽⁴⁾
	OP804SL	7.0	-	22		
	OP805SL	15	-	-		
	OP800WSL	0.3	-	3		
	OP801WSL	0.5	-	2		
	OP802WSL	2.5	-	3		
	OP830SL	15	-	-		V _{CE} = 5 V, E _E = 0.25 mW/cm ²⁽²⁾⁽³⁾⁽⁴⁾
	OP830WSL	4	-	-		
I _{CEO}	Collector Dark Current					
	OP800 (SL, WSL)	-	-	100	nA	V _{CE} = 10 V, E _E = 0
	OP830 (SL, WSL)	-	-	1		
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage					
	OP800 (SL, WSL)	30	-	-	V	I _C = 100 µA
	OP830 (SL, WSL)	15	-	-		
V _{(BR)CBO}	Collector-Base Breakdown Voltage [applies to OP800SL only]	30	-	-	V	I _C = 100 µA
V _{(BR)ECO}	Emitter-Collector Breakdown Voltage	5.0	-	-	V	I _E = 100 µA
V _{(BR)EBO}	Emitter-Base Breakdown Voltage [applies to OP800SL only]	5.0	-	-	V	I _E = 100 µA
V _{CE(SAT)} ⁽³⁾	Collector-Emitter Saturation Voltage					
	OP800WSL	-	-	0.4		I _C = .4 mA, E _E = 2.5 mW/cm ²⁽⁴⁾ I _C = 400 µA, E _E = 2.5 mW/cm ²⁽⁴⁾ I _C = 1 mA, E _E = 0.25 mW/cm ²⁽⁴⁾ I _C = 1.0 mA, E _E = 0.25 mW/cm ²⁽⁴⁾
	OP800SL	-	-	0.4		
	OP830SL	-	-	1.2		
	OP830WSL	-	-	1.2		
t _r	Rise Time	-	7	-	µs	V _{CC} = 5 V, I _C = 0.80 mA, R _L = 100 Ω (See Test Circuit)
t _f	Fall Time	-	7	-	µs	

Notes:

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3. Junction temperature maintained at 25° C.
4. Light source is an unfiltered tungsten bulb operating at CT = 2870 K or equivalent infrared source.

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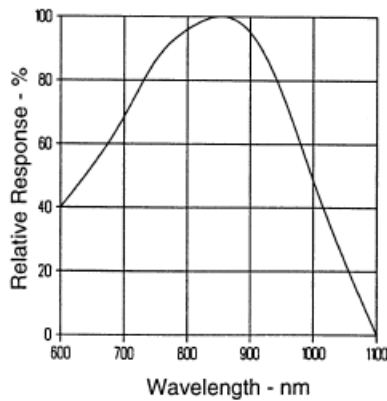
Obsolete (OP800SL)



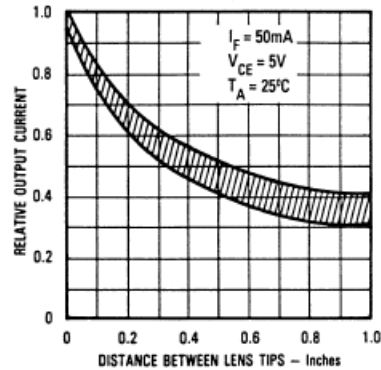
Performance

OP800SL Series

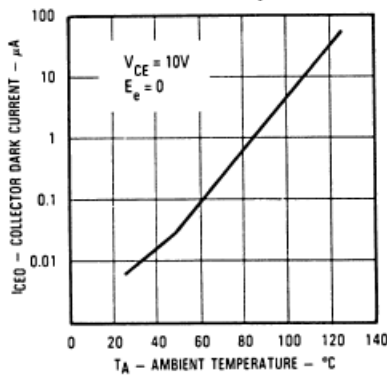
Typical Spectral Response



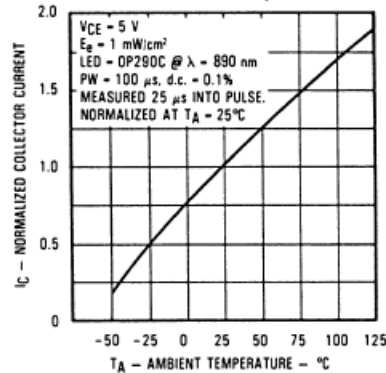
Coupling Characteristics of OP130 and OP800SL



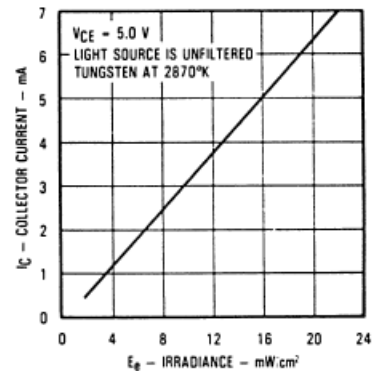
Collector Dark Current vs. Ambient Temperature



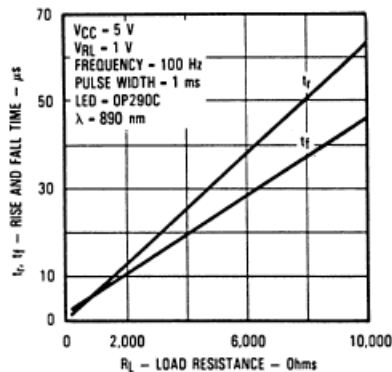
Normalized Collector Current vs. Ambient Temperature



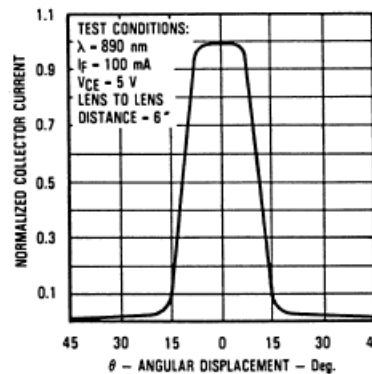
Collector Current vs. Irradiance



Rise and Fall Time vs. Load Resistance



Normalized Collector Current vs. Angular Displacement



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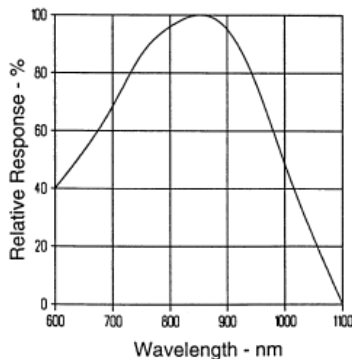
Obsolete (OP800SL)



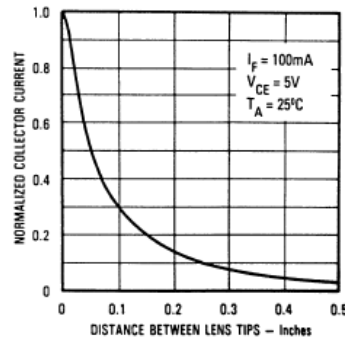
Performance

OP800WSL Series

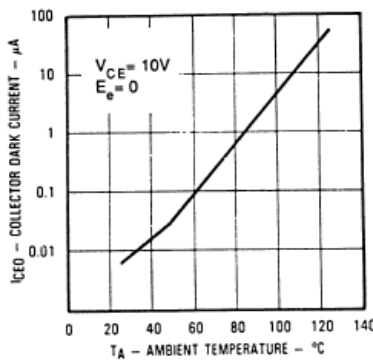
Typical Spectral Response



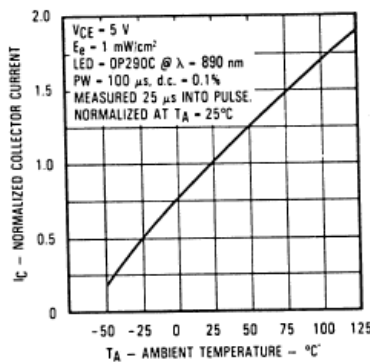
Coupling Characteristics of OP130W and OP800W



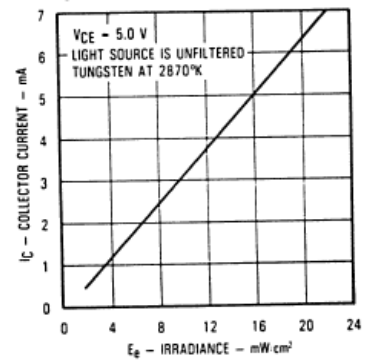
Collector Dark Current vs. Ambient Temperature



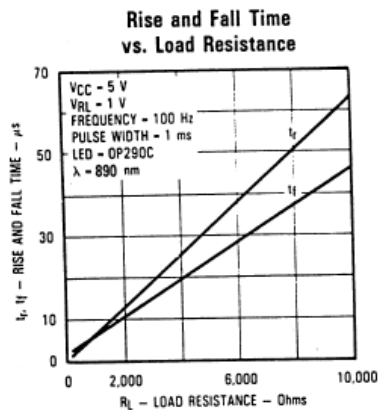
Normalized Collector Current vs. Ambient Temperature



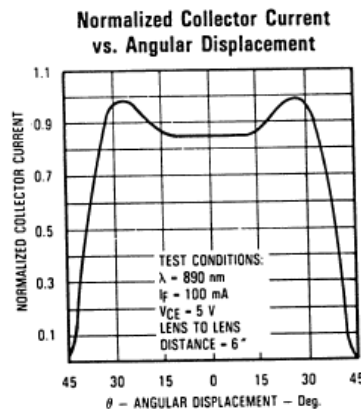
Collector Current vs. Irradiance



Rise and Fall Time vs. Load Resistance



Normalized Collector Current vs. Angular Displacement



Switching Time Test Circuit

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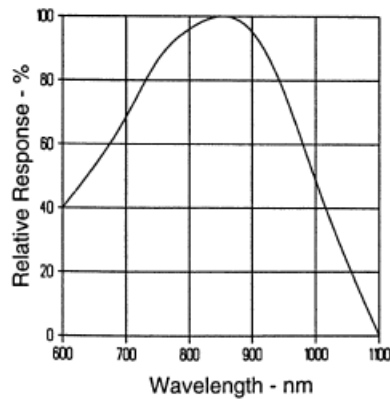
Obsolete (OP800SL)



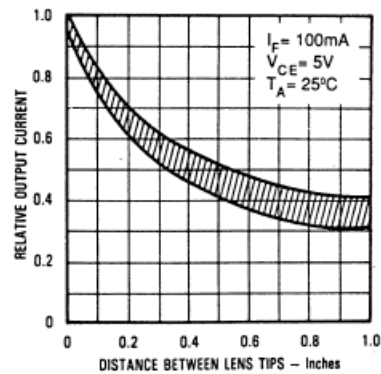
Performance

OP830SL Series

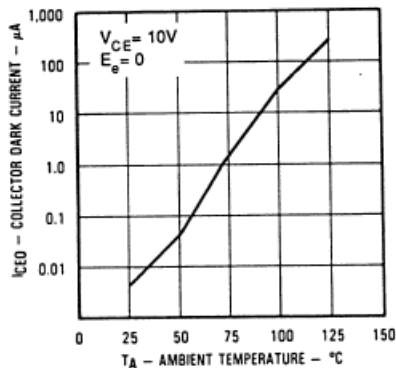
Typical Spectral Response



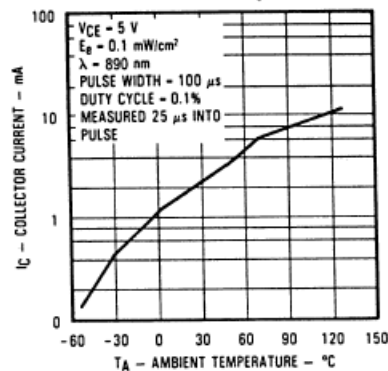
Coupling Characteristics of OP130 and OP830



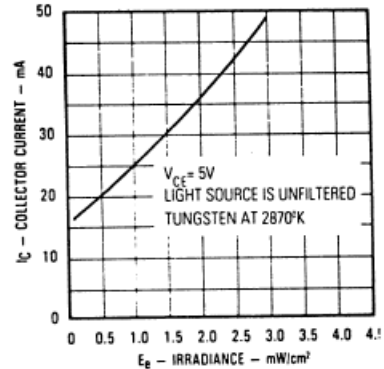
Collector Dark Current vs. Ambient Temperature



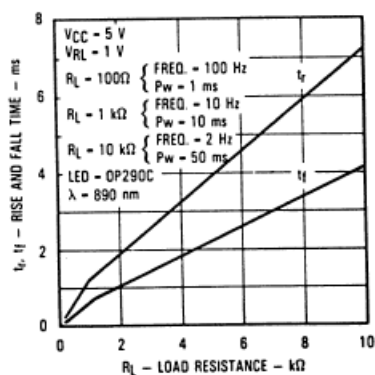
Collector Current vs. Ambient Temperature



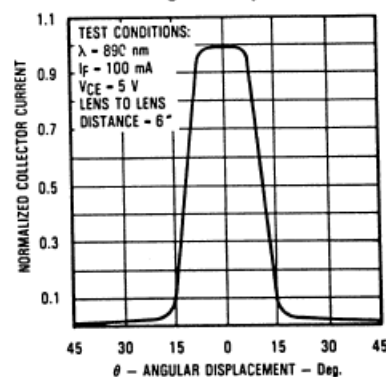
Collector Current vs. Irradiance



Rise and Fall Time vs. Load Resistance



Normalized Collector Current vs. Angular Displacement



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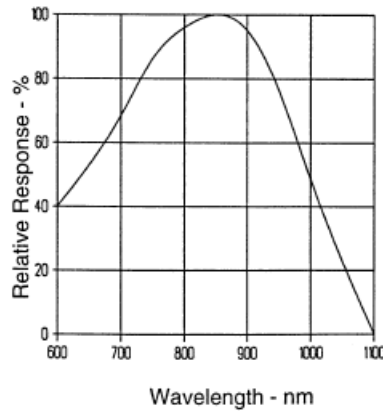
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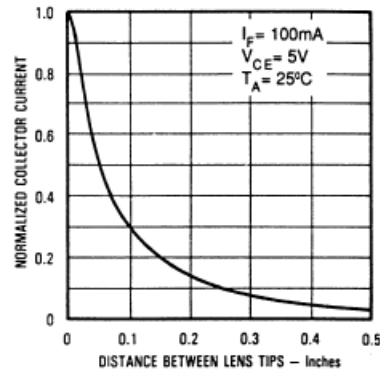
Performance

OP830WSL Series

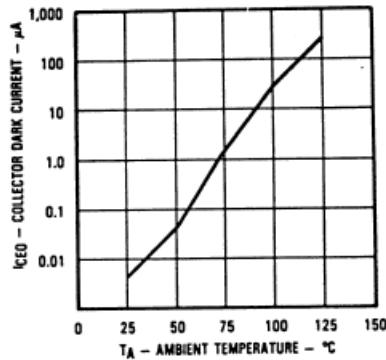
Typical Spectral Response



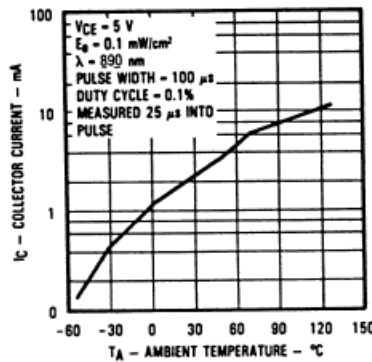
Coupling Characteristics of OP130W and OP830WSL



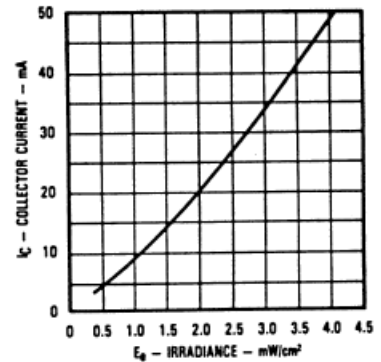
Collector Dark Current vs. Ambient Temperature



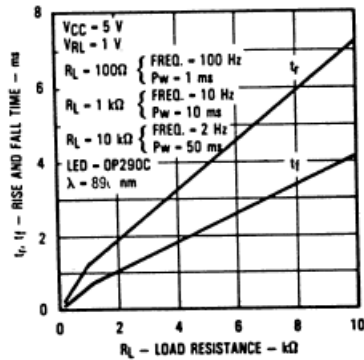
Collector Current vs. Ambient Temperature



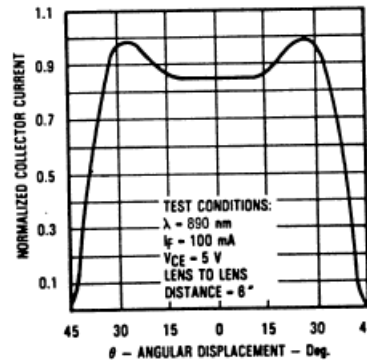
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